











CSD17318Q2

SLPS667A - FEBRUARY 2017-REVISED JULY 2017

# **CSD17318Q2 30-V N-Channel NexFET™ Power MOSFET**

#### **Features**

- Optimized for 5-V Gate Drive
- Low Capacitance and Charge
- Low R<sub>DS(ON)</sub>
- Low-Thermal Resistance
- Lead Free
- **RoHS Compliant**
- Halogen Free
- SON 2-mm x 2-mm Plastic Package

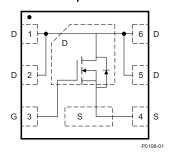
### **Applications**

- Storage, Tablets, and Handheld Devices
- Optimized for Load Switch Applications
- **DC-DC Converters**
- Battery and Load Management Applications

### Description

This 30-V, 12.6-m $\Omega$ , 2-mm × 2-mm SON NexFET<sup>TM</sup> power MOSFET is designed to minimize losses in power conversion applications and optimized for 5-V gate drive applications. The 2-mm x 2-mm SON offers excellent thermal performance for the size of the package.





#### **Product Summary**

$T_A = 25^{\circ}$	°C	TYPICAL VA	UNIT		
$V_{DS}$	Drain-to-Source Voltage	Orain-to-Source Voltage 30			
$Q_g$	Gate Charge Total (4.5 V)	6.0		nC	
$Q_{gd}$	Gate Charge Gate-to-Drain	1.3	nC		
		$V_{GS} = 2.5 \text{ V}$	20		
R <sub>DS(on)</sub>	Drain-to-Source On-Resistance	V <sub>GS</sub> = 4.5 V	13.9	mΩ	
		$V_{GS} = 8 V$	12.6		
V <sub>GS(th)</sub>	Threshold Voltage	0.9		V	

#### Device Information<sup>(1)</sup>

PART NUMBER	QTY	MEDIA	PACKAGE	SHIP		
CSD17318Q2	3000		SON	Tape		
CSD17318Q2T	250	7-Inch Reel	2.00-mm x 2.00-mm Plastic Package	and Reel		

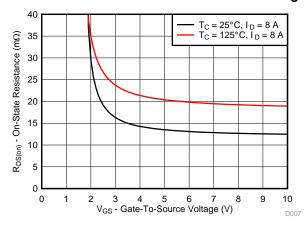
(1) For all available packages, see the orderable addendum at the end of the data sheet.

#### **Absolute Maximum Ratings**

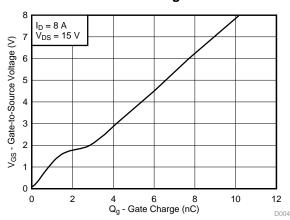
T <sub>A</sub> = 2	5°C	VALUE	UNIT	
$V_{DS}$	Drain-to-Source Voltage	30	٧	
$V_{\text{GS}}$	Gate-to-Source Voltage	±10	V	
	Continuous Drain Current (Package Limited)	21.5		
I <sub>D</sub>	Continuous Drain Current (Silicon Limited), $T_C = 25$ °C	25	Α	
	Continuous Drain Current <sup>(1)</sup>	10		
I <sub>DM</sub>	Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>	68	Α	
п	Power Dissipation <sup>(1)</sup>	2.5	W	
$P_D$	Power Dissipation, T <sub>C</sub> = 25°C	16	VV	
$T_J$ , $T_{STG}$	Operating Junction, Storage Temperature	-55 to 150	ô	
E <sub>AS</sub>	Avalanche Energy, Single Pulse, ID = 12.4 A, L = 0.1 mH, R_G = 25 $\Omega$	7.7	mJ	

- (1) Typical  $R_{\theta JA} = 55^{\circ}C/W$  on a 1-in<sup>2</sup>, 2-oz Cu pad on a 0.06-in thick FR4 PCB.
- (2) Max  $R_{\theta JC} = 7^{\circ}C/W$ , pulse duration  $\leq 100 \mu s$ , duty cycle  $\leq 1\%$ .

#### On-State Resistance vs Gate to Source Voltage



#### **Gate Charge**





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# 4 Revision History

Cł	nanges from Original (February 2017) to Revision A	Pag	јe
•	Updated the <i>Mechanical Data</i> drawings		8

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# 5 Specifications

#### 5.1 Electrical Characteristics

 $T_{\Delta} = 25^{\circ}C$  (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC	CHARACTERISTICS					•
$BV_{DSS}$	Drain-to-source voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
I <sub>DSS</sub>	Drain-to-source leakage	$V_{GS} = 0 \text{ V}, V_{DS} = 24 \text{ V}$			1	μΑ
I <sub>GSS</sub>	Gate-to-source leakage	$V_{DS} = 0 \text{ V}, V_{GS} = 10 \text{ V}$			100	nA
$V_{GS(th)}$	Gate-to-source threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	0.6	0.9	1.2	V
		$V_{GS} = 2.5 \text{ V}, I_D = 8 \text{ A}$		20	30	
R <sub>DS(on)</sub>	Drain-to-source on-resistance	$V_{GS} = 4.5 \text{ V}, I_D = 8 \text{ A}$		13.9	16.9	$m\Omega$
		$V_{GS} = 8 \text{ V}, I_D = 8 \text{ A}$		12.6	15.1	
g <sub>fs</sub>	Transconductance	$V_{DS} = 3 \text{ V}, I_{D} = 8 \text{ A}$		42		S
DYNAMI	C CHARACTERISTICS					
C <sub>iss</sub>	Input capacitance			676	879	рF
C <sub>oss</sub>	Output capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 15 \text{ V},$ f = 1  MHz		71	92	pF
C <sub>rss</sub>	Reverse transfer capacitance	) - 1 Will 2		39	51	pF
$R_G$	Series gate resistance			1.0	2.0	Ω
Qg	Gate charge total (4.5 V)			6.0		nC
$Q_{gd}$	Gate charge gate-to-drain	V <sub>DS</sub> = 15 V,		1.3		nC
Q <sub>gs</sub>	Gate charge gate-to-source	I <sub>D</sub> = 8 A		1.5		nC
Q <sub>g(th)</sub>	Gate charge at Vth			0.7		nC
Q <sub>oss</sub>	Output charge	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}$		2.7		nC
t <sub>d(on)</sub>	Turnon delay time			5		ns
t <sub>r</sub>	Rise time	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		16		ns
t <sub>d(off)</sub>	Turnoff delay time	$I_D = 8 \text{ A}, R_G = 2 \Omega$		13		ns
t <sub>f</sub>	Fall time			4		ns
DIODE (	CHARACTERISTICS				•	
V <sub>SD</sub>	Diode forward voltage	I <sub>SD</sub> = 8 A, V <sub>GS</sub> = 0 V		8.0	1.0	V
Q <sub>rr</sub>	Reverse recovery charge	V <sub>DD</sub> = 15 V, I <sub>F</sub> = 8 A,		2.9		nC
t <sub>rr</sub>	Reverse recovery time	di/dt = 300 A/μs		12		ns

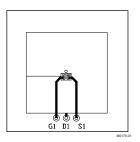
### 5.2 Thermal Characteristics

 $T_A = 25^{\circ}C$  (unless otherwise noted)

	PARAMETER	MIN	TYP MAX	UNIT
$R_{\theta JC}$	Thermal resistance junction-to-case <sup>(1)</sup>		7.9	°C/W
$R_{\theta JA}$	Thermal resistance junction-to-ambient (1)(2)		6	°C/W

 <sup>(1)</sup> R<sub>θ,JC</sub> is determined with the device mounted on a 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu pad on a 1.5-in x 1.5-inch (3.81-cm x 3.81-cm), 0.06-in (1.52-mm) thick FR4 PCB. R<sub>θ,JC</sub> is specified by design, whereas R<sub>θ,JA</sub> is determined by the user's board design.
 (2) Device mounted on FR4 material with 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu.





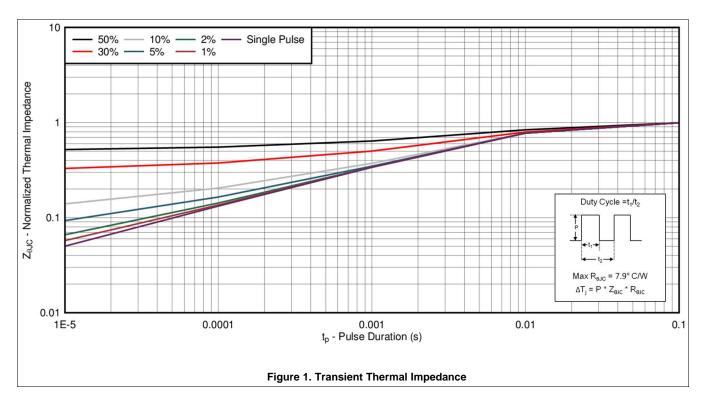
Max  $R_{\theta JA} = 65^{\circ}\text{C/W}$  when mounted on 1 in<sup>2</sup> (6.45 cm<sup>2</sup>) of 2-oz (0.071-mm) thick Cu.

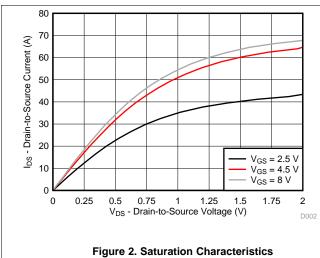


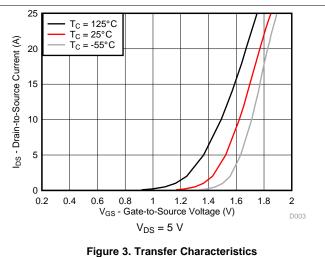
Max  $R_{\theta JA} = 250^{\circ} \text{C/W}$  when mounted on a minimum pad area of 2-oz (0.071-mm) thick Cu.

### 5.3 Typical MOSFET Characteristics

 $T_A = 25$ °C (unless otherwise noted)





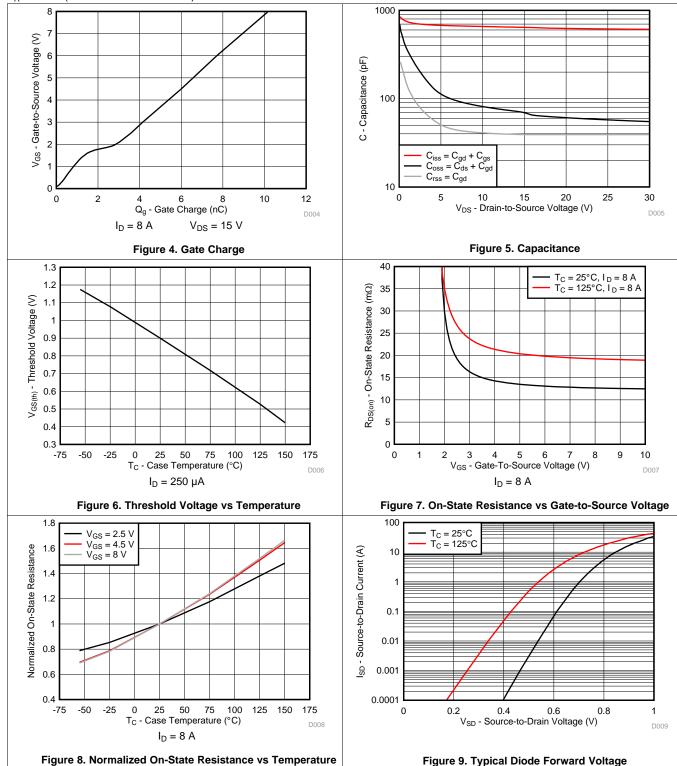


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### **Typical MOSFET Characteristics (continued)**

 $T_A = 25$ °C (unless otherwise noted)



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### **Typical MOSFET Characteristics (continued)**

 $T_A = 25$ °C (unless otherwise noted)

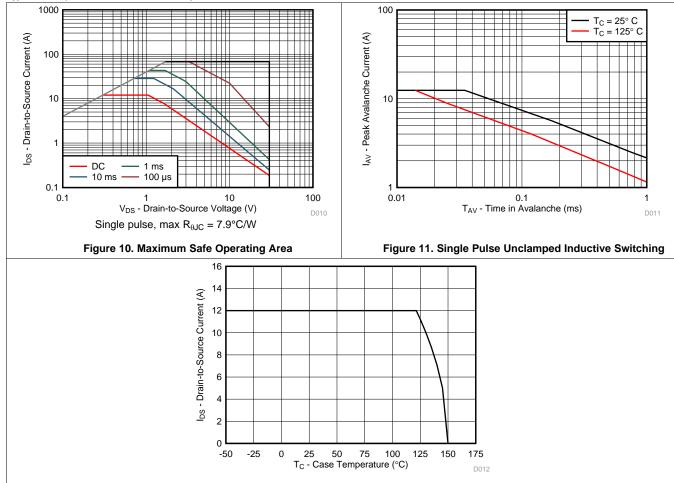


Figure 12. Maximum Drain Current vs Temperature



### 6 Device and Documentation Support

### 6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 6.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

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**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 6.3 Trademarks

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#### 6.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### 6.5 Glossary

SLYZ022 — TI Glossary.

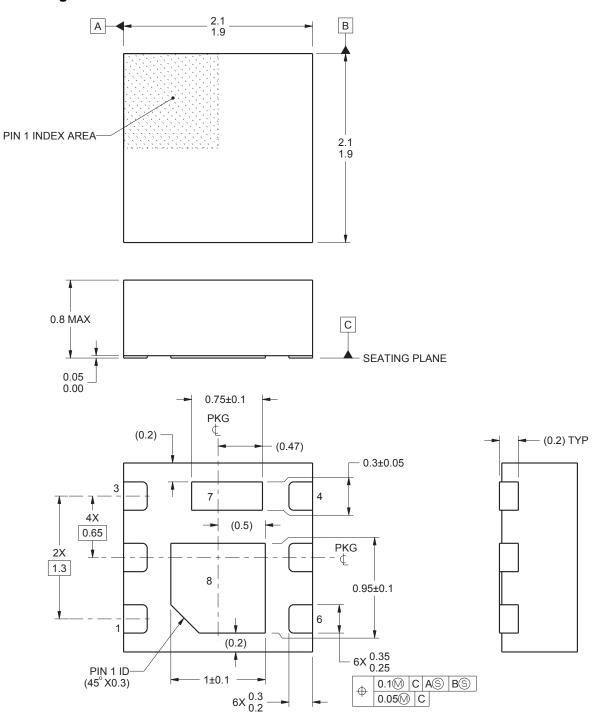
This glossary lists and explains terms, acronyms, and definitions.

Product Folder Links: CSD17318Q2



#### 7 Mechanical Data

### 7.1 Q2 Package Dimensions



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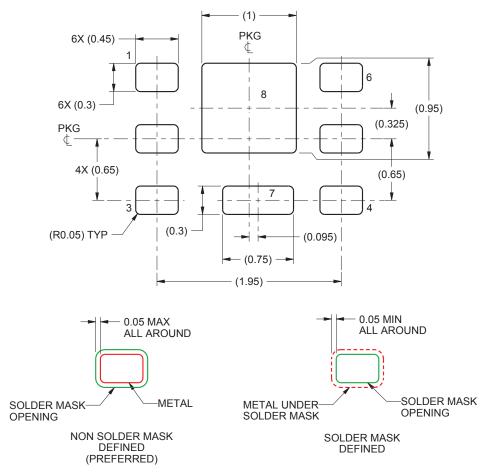
- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pads must be soldered to the printed circuit board for thermal and mechanical performance.

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### **Q2 Package Dimensions (continued)**

### 7.1.1 Recommended PCB Pattern



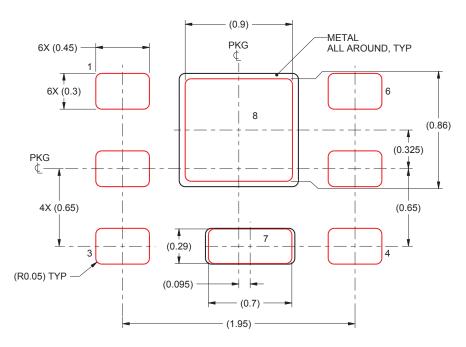
**SOLDER MASK DETAILS** 

1. This package is designed to be soldered to a thermal pad on the board. For more information, see *QFN/SON PCB Attachment* (SLUA271).



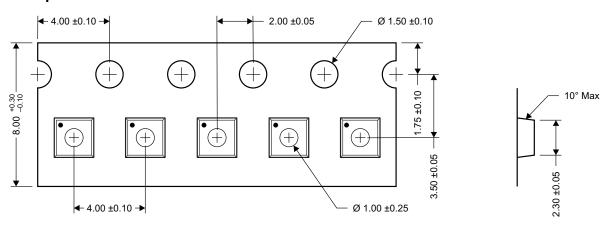
### **Q2 Package Dimensions (continued)**

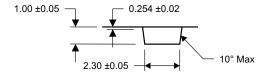
#### 7.1.2 Recommended Stencil Pattern



1. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

### 7.2 Q2 Tape and Reel Information





M0168-01

Notes: 1. Measured from centerline of sprocket hole to centerline of pocket.

- 2. Cumulative tolerance of 10 sprocket holes is ±0.20.
- 3. Other material available.
- 4. Typical SR of form tape Max  $10^9$  OHM/SQ.
- 5. All dimensions are in mm, unless otherwise specified.

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### PACKAGE OPTION ADDENDUM

4-Aug-2017

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	_	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD17318Q2	ACTIVE	WSON	DQK	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU   CU SN	Level-1-260C-UNLIM	-55 to 150	1718	Samples
CSD17318Q2T	ACTIVE	WSON	DQK	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU   CU SN	Level-1-260C-UNLIM	-55 to 150	1718	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

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- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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# PACKAGE MATERIALS INFORMATION

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### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

All difficusions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD17318Q2	WSON	DQK	6	3000	180.0	8.4	2.3	2.3	1.0	4.0	8.0	Q1
CSD17318Q2	WSON	DQK	6	3000	180.0	9.5	2.3	2.3	1.0	4.0	8.0	Q1
CSD17318Q2T	WSON	DQK	6	250	180.0	9.5	2.3	2.3	1.0	4.0	8.0	Q1
CSD17318Q2T	WSON	DQK	6	250	180.0	8.4	2.3	2.3	1.0	4.0	8.0	Q1

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\*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins SPQ		Length (mm)	Width (mm)	Height (mm)
CSD17318Q2	WSON	DQK	6	3000	550.0	455.0	55.0
CSD17318Q2	WSON	DQK	6	3000	189.0	185.0	36.0
CSD17318Q2T	WSON	DQK	6	250	189.0	185.0	36.0
CSD17318Q2T	WSON	DQK	6	250	550.0	455.0	55.0

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